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| S1 | 252 | semiconductor with (fab fabricat\$4) with (simulat\$4 model\$4) | USPAT | OR | OFF | 2005/07/20 13:11 |
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| S3 | 1 | ("6154717").PN. | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/07/20 13:24 |
| S4 | 6 | "10/989011" "10/780938" "10/668621" "09/891400" "09/781421" "09/519856" | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/07/20 13:29 |
| S5 | 1428 | 703/2.ccls. | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/07/20 13:29 |
| S6 | 146 | S5 and (diffusion impurit\$3 impure) | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/07/20 13:31 |
| S7 | 191 | ("pile-up" (pile adj up)) same (diffusion diffus\$4) | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/07/20 13:32 |
| S8 | 1 | 10/059176 | US-PGPUB | OR | OFF | 2005/07/20 16:01 |
| S10 | 1 | "6581028".pn. | USPAT | OR | OFF | 2005/07/20 17:15 |
| S11 | 245 | reverse adj short adj channel | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/07/20 17:15 |
| S12 | 21 | ("5930494" "5819073" "5557710" "5684723" "6195790" "5148379" "6360190" "6242272" "6006026" "6080200" "5828586" "5889687" "6185472" "5819073" "6041424" "4584662" "6182270" "6011914" "6144932" "6360190" "6154717" "6505147" "6144929").pn. | USPAT | OR | OFF | 2005/07/21 16:42 |

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| S13 | 13 | ("5103415" "5671395" "5675522" "5677846" "5774696" "5784302" "5819073" "5828586" "5889680" "5930494" "5963732" "6006026" "6011914").PN. | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/07/21 11:01 |
| S14 | 19 | (US-4607530-\$ or US-6594625-\$ or US-6006026-\$ or US-6684181-\$ or US-6327555-\$ or US-6285970-\$ or US-6154718-\$ or US-6154717-\$ or US-6148276-\$ or US-6144929-\$ or US-6120548-\$ or US-6041174-\$ or US-5999719-\$ or US-6581028-\$ or US-5557710-\$ or US-6242272-\$ or US-6505147-\$ or US-5889687-\$ or US-5930494-\$).did. | USPAT | OR | OFF | 2005/07/21 11:53 |
| S15 | 1 | S14 and (SiO) | USPAT | OR | OFF | 2005/07/21 11:53 |
| S16 | 9 | S14 and layer | USPAT | OR | OFF | 2005/07/21 12:05 |
| S17 | 5 | S14 and (source drain) | USPAT | OR | OFF | 2005/07/21 12:10 |
| S18 | 4 | S17 and distance | USPAT | OR | OFF | 2005/07/21 13:17 |
| S19 | 1 | "6080200".pn. | USPAT | OR | OFF | 2005/07/21 13:11 |
| S20 | 258 | (impurity adj diffusion) same (source drain) same (distance length) | USPAT | OR | OFF | 2005/07/21 13:23 |
| S21 | 39 | S20 and (simulat\$4 model\$4) | USPAT | OR | OFF | 2005/07/21 13:18 |

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